International
IOR Rectifier

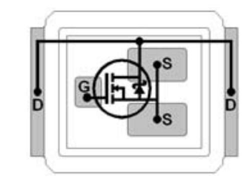
PD - 94574C

IRF6607

HEXFET® Power MOSFET

- Application Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- Low Conduction Losses
- High Cdv/dt Immunity
- Low Profile (<0.7 mm)
- Dual Sided Cooling Compatible
- Compatible with existing Surface Mount Techniques

V_{DSS}	$R_{DS(on)}$ max	Qg(typ.)
30V	3.3mΩ@V_{GS} = 10V	50nC
	4.4mΩ@V_{GS} = 4.5V	



MT


DirectFET™ ISOMETRIC

Applicable DirectFET Outline and Substrate Outline (see p.9,10 for details)

SQ	SX	ST		MQ	MX	MT				

Description

The IRF6607 combines the latest HEXFET® Power MOSFET Silicon technology with the advanced DirectFET™ packaging to achieve the lowest on-state resistance in a package that has the footprint of an SO-8 and only 0.7 mm profile. The DirectFET package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and process. The DirectFET package allows dual sided cooling to maximize thermal transfer in power systems, IMPROVING previous best thermal resistance by 80%.

The IRF6607 balances both low resistance and low charge along with ultra low package inductance to reduce both conduction and switching losses. The reduced total losses make this product ideal for high efficiency DC-DC converters that power the latest generation of processors operating at higher frequencies. The IRF6607 has been optimized for parameters that are critical in synchronous buck converters including Rds(on), gate charge and Cdv/dt-induced turn on immunity. The IRF6607 offers particularly low Rds(on) and high Cdv/dt immunity for synchronous FET applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	±12	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V ④	94	A
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V ④	27	
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V ⑦	22	
I_{DM}	Pulsed Drain Current ①	220	
P_D @T_A = 25°C	Power Dissipation ④	3.6	W
P_D @T_A = 70°C	Power Dissipation ④	2.3	
P_D @T_C = 25°C	Power Dissipation ⑦	42	
	Linear Derating Factor	0.029	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-40 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{θJA}$	Junction-to-Ambient ④⑧	–––	35	°C/W
$R_{θJA}$	Junction-to-Ambient ⑤⑧	12.5	–––	
$R_{θJA}$	Junction-to-Ambient ⑥⑧	20	–––	
$R_{θJC}$	Junction-to-Case ⑦⑧	–––	3.0	
$R_{θJ-PCB}$	Junction-to-PCB Mounted	–––	1.0	

Notes ① through ⑧ are on page 10

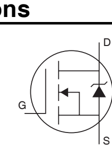
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	---	---	V	V_{GS} = 0V, I_D = 250μA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	---	29	---	mV/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	---	2.5	3.3	mΩ	V_{GS} = 10V, I_D = 25A ③
		---	3.4	4.4		V_{GS} = 4.5V, I_D = 20A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.3	---	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	---	-5.3	---	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	---	---	30	μA	V_{DS} = 24V, V_{GS} = 0V
		---	---	50	μA	V_{DS} = 30V, V_{GS} = 0V
		---	---	100		V_{DS} = 24V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	---	---	100	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	---	---	-100		V_{GS} = -12V
gfs	Forward Transconductance	120	---	---	S	V_{DS} = 15V, I_D = 20A
Q_g	Total Gate Charge	---	50	75		
Q_{gs1}	Pre-Vth Gate-to-Source Charge	---	13	---		V_{DS} = 15V
Q_{gs2}	Post-Vth Gate-to-Source Charge	---	4.0	---	nC	V_{GS} = 4.5V
Q_{gd}	Gate-to-Drain Charge	---	16	---		I_D = 20A
Q_{godr}	Gate Charge Overdrive	---	18	---		See Fig. 16
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	---	20	---		
Q_{oss}	Output Charge	---	30	---	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	---	0.86	1.9	Ω	
$t_{d(on)}$	Turn-On Delay Time	---	60	---		V_{DD} = 15V, V_{GS} = 4.5V ③
t_r	Rise Time	---	8.0	---		I_D = 20A
$t_{d(off)}$	Turn-Off Delay Time	---	32	---	ns	Clamped Inductive Load
t_f	Fall Time	---	13	---		
C_{iss}	Input Capacitance	---	6930	---		V_{GS} = 0V
C_{oss}	Output Capacitance	---	1260	---	pF	V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	---	510	---		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	---	51	mJ
I_{AR}	Avalanche Current ①	---	20	A
E_{AR}	Repetitive Avalanche Energy ①	---	0.36	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	---	---	38	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	---	---	220		
V_{SD}	Diode Forward Voltage	---	1.0	1.3	V	T_J = 25°C, I_S = 20A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	---	46	69	ns	T_J = 25°C, I_F = 20A
Q_{rr}	Reverse Recovery Charge	---	54	81	nC	di/dt = 100A/μs ③

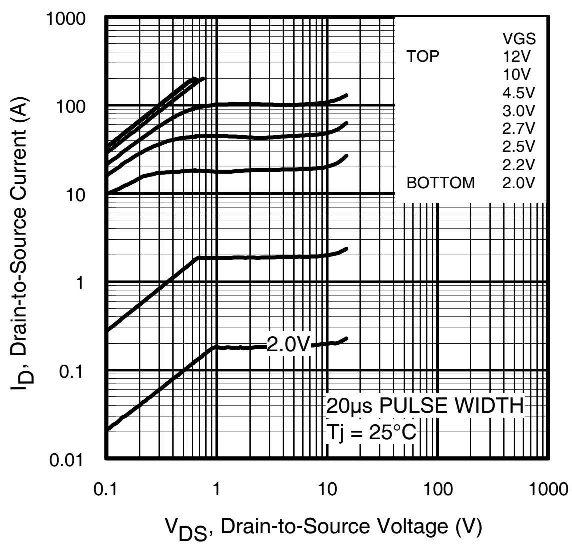


Fig 1. Typical Output Characteristics

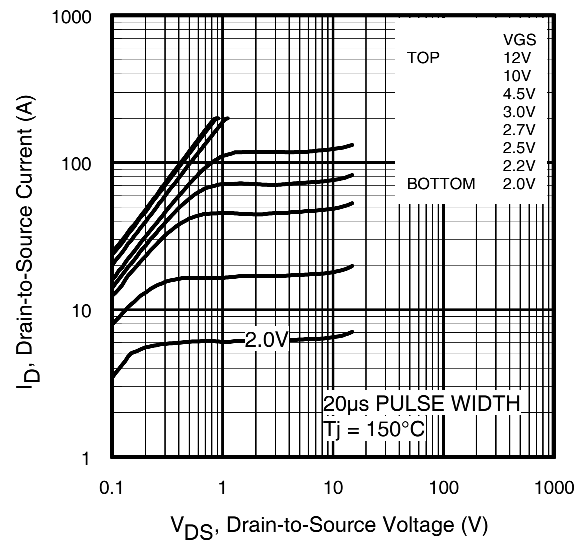


Fig 2. Typical Output Characteristics

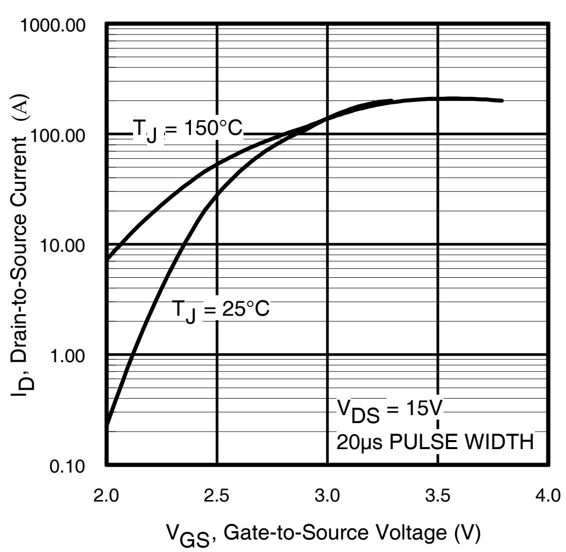


Fig 3. Typical Transfer Characteristics

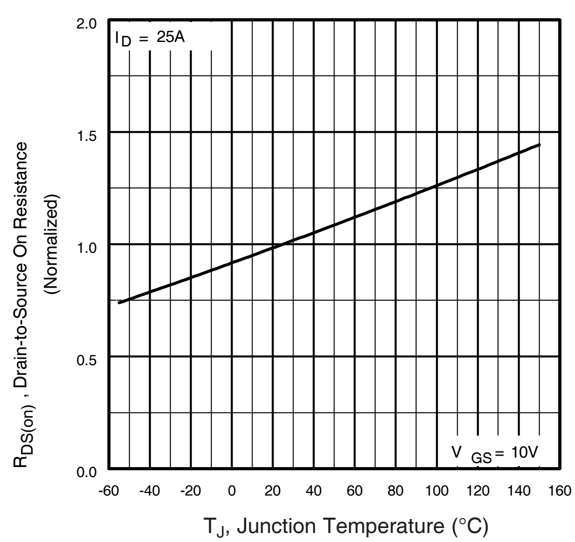


Fig 4. Normalized On-Resistance vs. Temperature

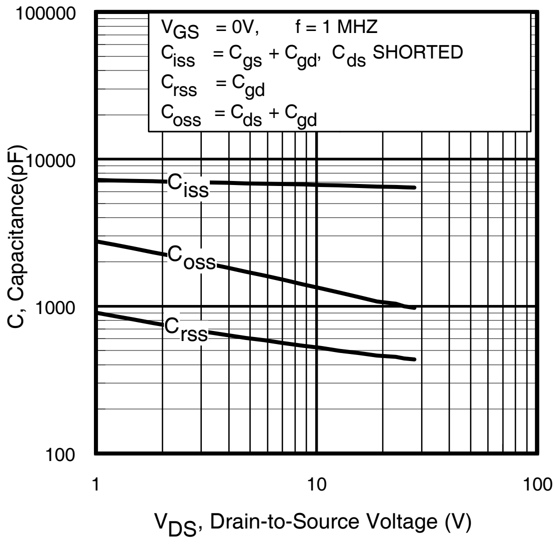


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

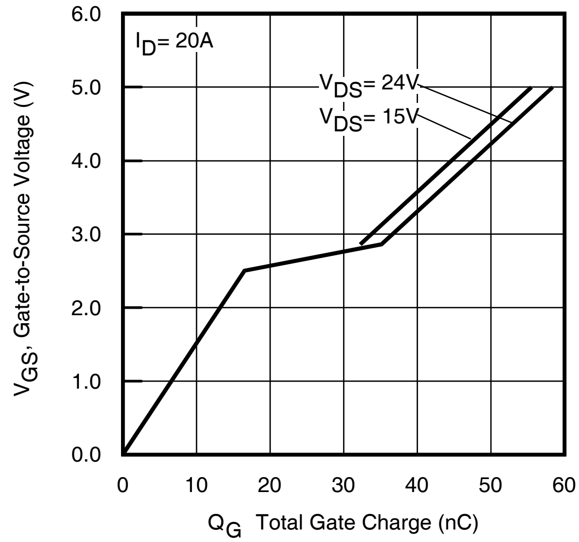


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

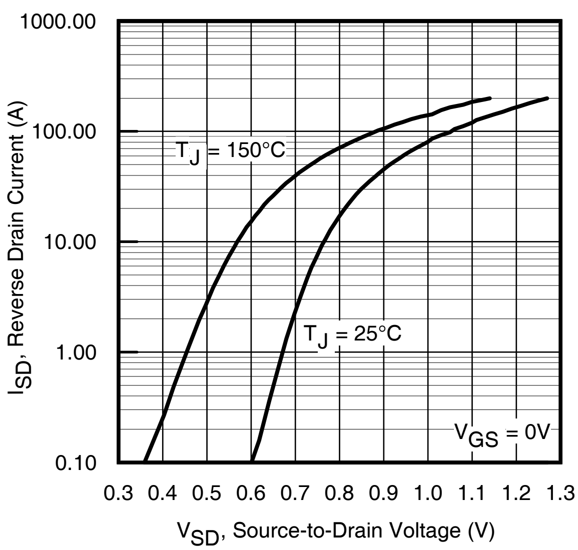


Fig 7. Typical Source-Drain Diode Forward Voltage

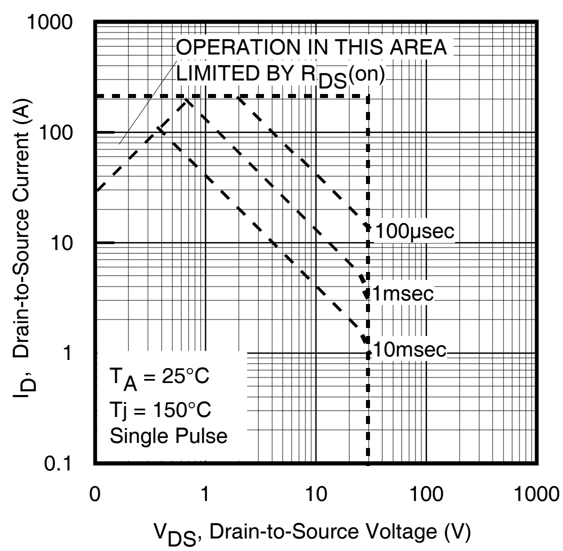


Fig 8. Maximum Safe Operating Area

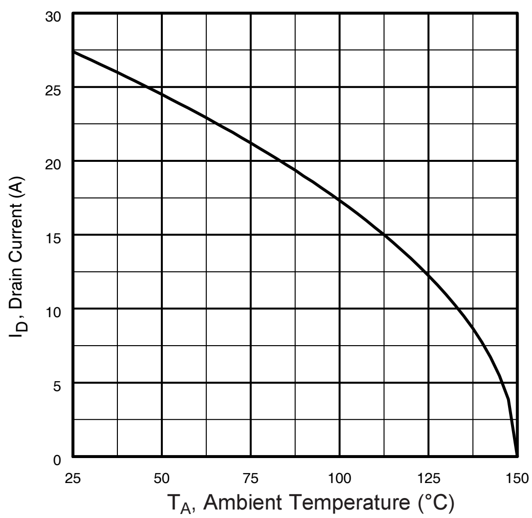


Fig 9. Maximum Drain Current Vs. Ambient Temperature

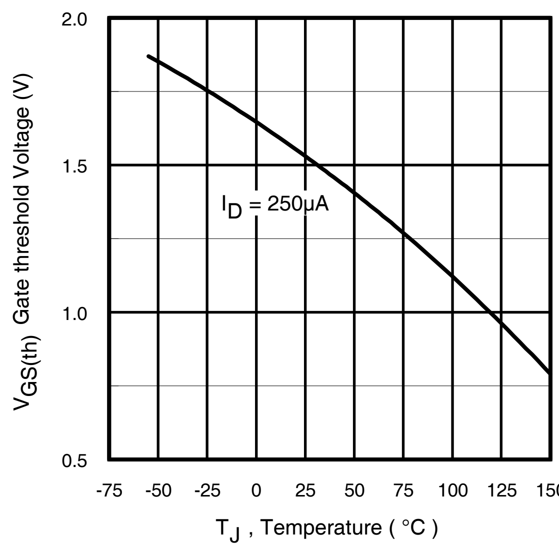


Fig 10. Threshold Voltage Vs. Temperature

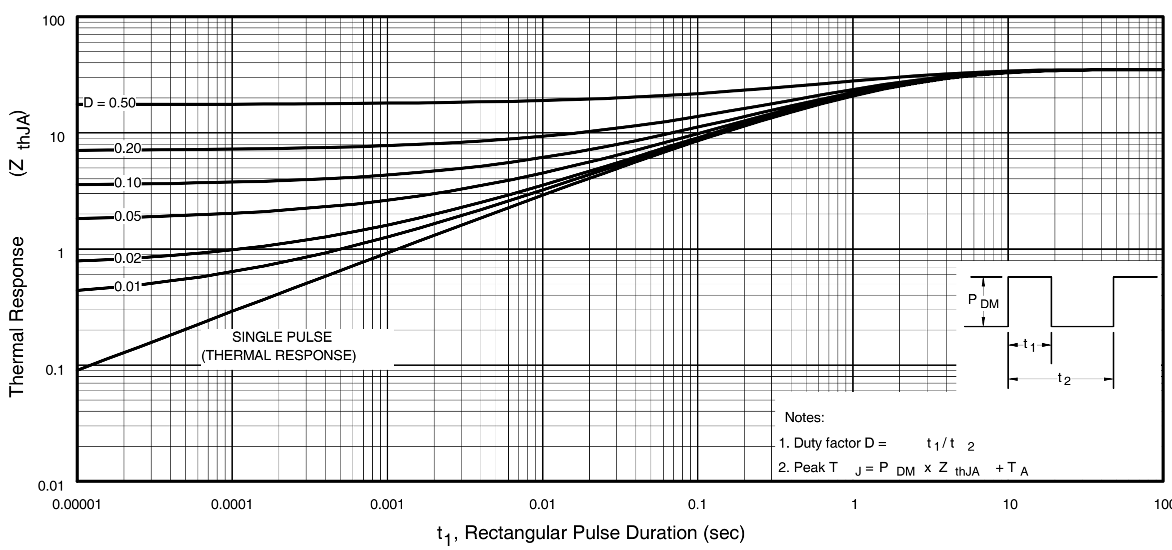


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

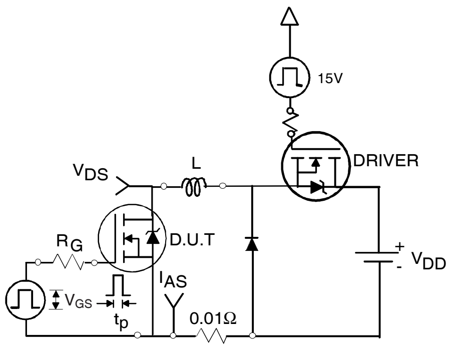


Fig 12a. Unclamped Inductive Test Circuit

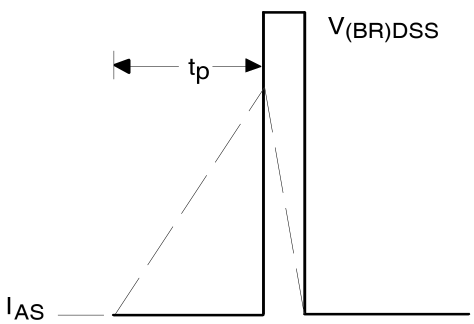


Fig 12b. Unclamped Inductive Waveforms

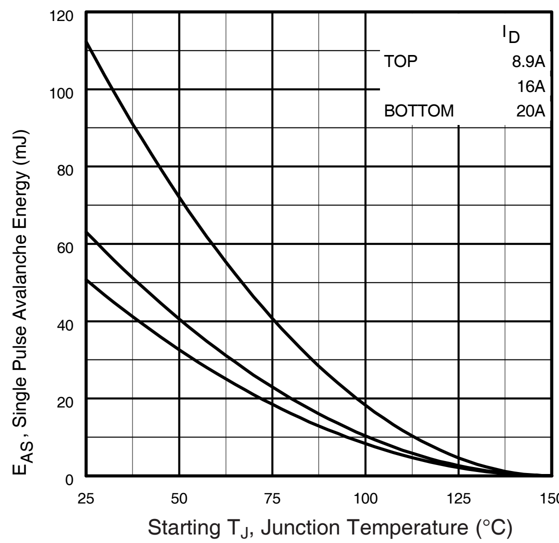


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

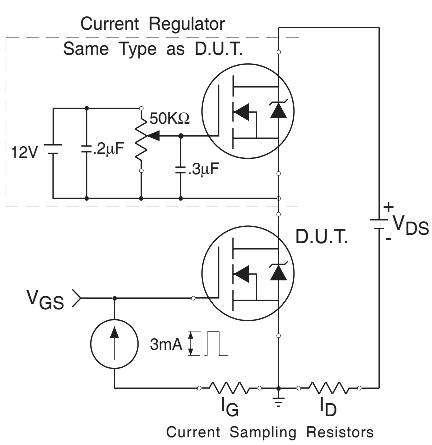


Fig 13. Gate Charge Test Circuit

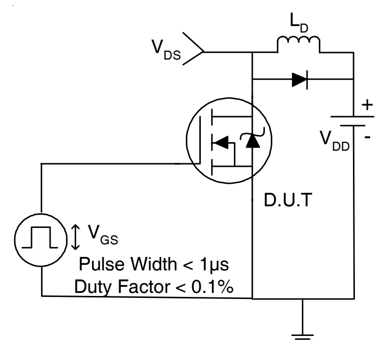


Fig 14a. Switching Time Test Circuit

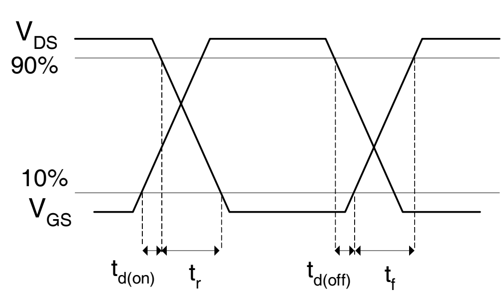
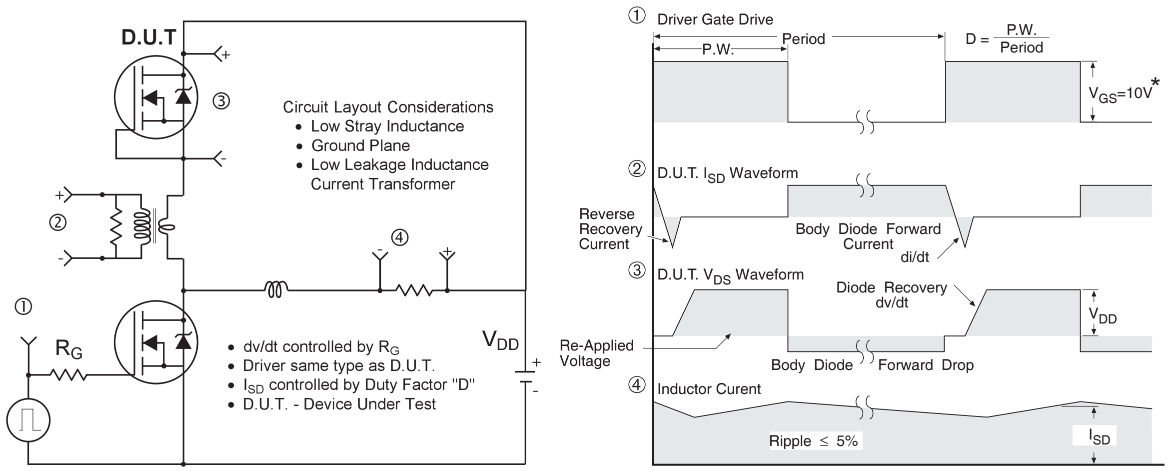


Fig 14b. Switching Time Waveforms



* V_{GS} = 5V for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

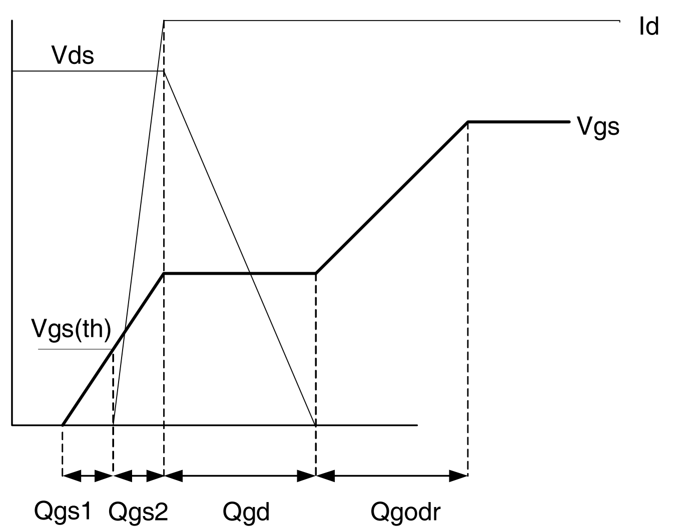
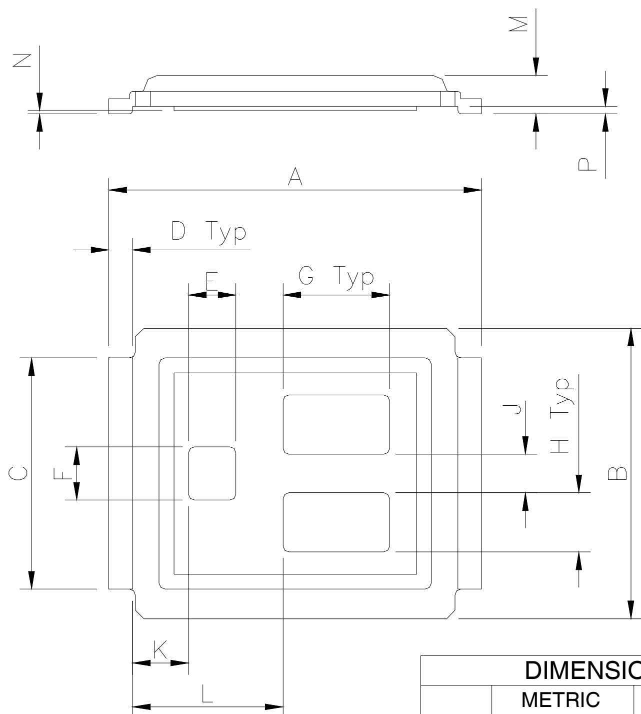


Fig 16. Gate Charge Waveform

DirectFET™ Outline Dimension, MT Outline (Medium Size Can, T-Designation).

Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET. This includes all recommendations for stencil and substrate designs.

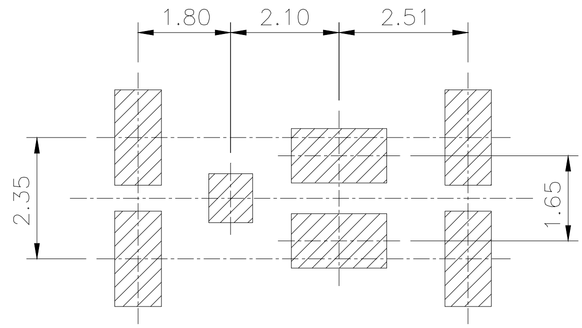


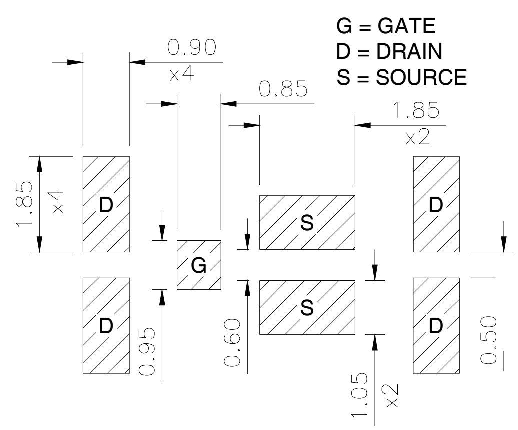
DIMENSIONS				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	6.25	6.35	0.246	0.250
B	4.80	5.05	0.189	0.199
C	3.85	3.95	0.152	0.156
D	0.35	0.45	0.014	0.018
E	0.78	0.82	0.031	0.032
F	0.88	0.92	0.035	0.036
G	1.78	1.82	0.070	0.072
H	0.98	1.02	0.039	0.040
J	0.63	0.67	0.025	0.026
K	0.88	1.01	0.035	0.039
L	2.46	2.63	0.097	0.104
M	0.59	0.70	0.023	0.028
N	0.03	0.08	0.001	0.003
P	0.08	0.17	0.003	0.007

DirectFET™ Substrate and PCB Layout, MT Outline (MediumSize Can, T-Designation).

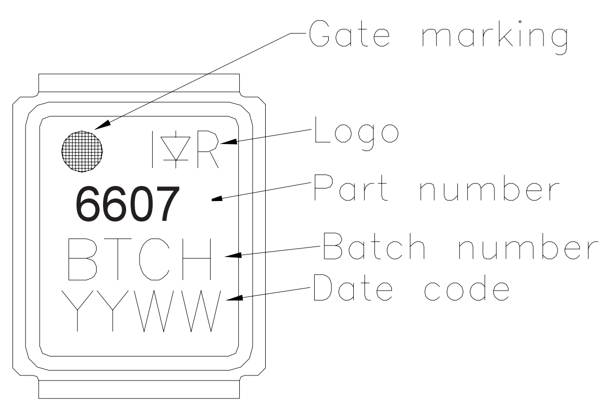
Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET.

This includes all recommendations for stencil and substrate designs.

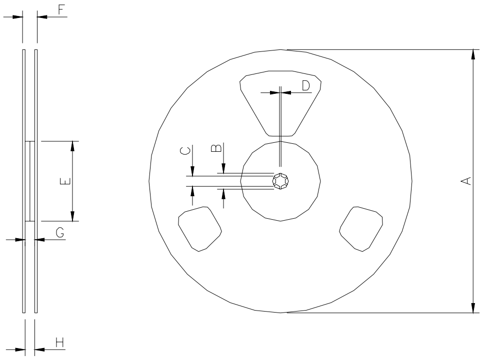


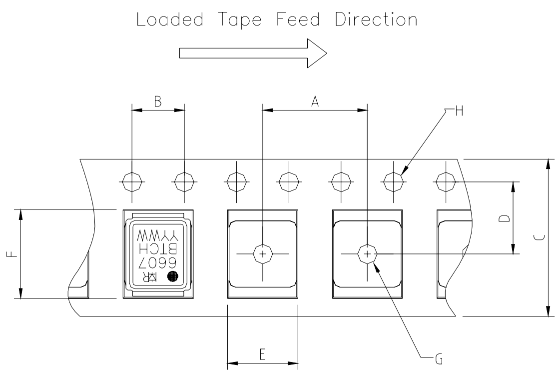


DirectFET™ Part Marking



DirectFET™ Tape & Reel Dimension (Showing component orientation).





NOTE: Controlling dimensions in mm
Std reel quantity is 4800 parts. (ordered as IRF6607). For 1000 parts on 7" reel, order IRF6607TR1

REEL DIMENSIONS								
	STANDARD OPTION **(QTY 4800)**				TR1 OPTION **(QTY 1000)**			
	METRIC		IMPERIAL		METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
A	330.0	N.C	12.992	N.C	177.77	N.C	6.9	N.C
B	20.2	N.C	0.795	N.C	19.06	N.C	0.75	N.C
C	12.8	13.2	0.504	0.520	13.5	12.8	0.53	0.50
D	1.5	N.C	0.059	N.C	1.5	N.C	0.059	N.C
E	100.0	N.C	3.937	N.C	58.72	N.C	2.31	N.C
F	N.C	18.4	N.C	0.724	N.C	13.50	N.C	0.53
G	12.4	14.4	0.488	0.567	11.9	12.01	0.47	N.C
H	11.9	15.4	0.469	0.606	11.9	12.01	0.47	N.C

NOTE: CONTROLLING DIMENSIONS IN MM

DIMENSIONS				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	7.90	8.10	0.311	0.319
B	3.90	4.10	0.154	0.161
C	11.90	12.30	0.469	0.484
D	5.45	5.55	0.215	0.219
E	5.10	5.30	0.201	0.209
F	6.50	6.70	0.256	0.264
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting $T_J = 25°C$, L = 0.25mH $R_G = 25\Omega$, $I_{AS} = 20A$.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ Surface mounted on 1 in. square Cu board.

⑤ Used double sided cooling , mounting pad.

⑥ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.

⑦ T_C measured with thermal couple mounted to top (Drain) of part.

⑧ R_θ is measured at T_J of approximately 90°C.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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Visit us at www.irf.com for sales contact information.12/05

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/